









5. *Dawber M., Scott J.F.* Negative differential resistivity and positive temperature coefficient of resistivity effect in the diffusion-limited current of ferroelectric thin-film capacitors // *Journal of Physics: Condensed Matter*. – 2004, т. 16, № 49, с. L515- L521.
6. *Chen B. et al.* Thickness and dielectric constant of dead layer in Pt/(Ba<sub>0.7</sub>Sr<sub>0.3</sub>)TiO<sub>3</sub>/YBa<sub>2</sub>Cu<sub>3</sub>O<sub>7-x</sub> capacitor // *Applied Physics Letters*. – 2004, v. 84, № 4, p. 583-585.
7. *Basceri C. et al.* The dielectric response as a function of temperature and film thickness of fiber-textured (Ba, Sr) TiO<sub>3</sub> thin films grown by chemical vapor deposition // *Journal of Applied Physics*. – 1997, т. 82. – №. 5, с. 2497-2504.
8. *Hwang C.S. et al.* Interface potential barrier height and leakage current behavior of Pt/(Ba, Sr) TiO<sub>3</sub>/Pt capacitors fabricated by sputtering process // *Integrated Ferroelectrics*. – 1996, т. 13, № 1-3, с. 157-177.
9. *Лавров П.П.* Влияние нарушенных слоев на диэлектрические свойства конденсаторных структур на основе сегнетоэлектрических пленок // *Российский технологический журнал* – 2016, т. 4, № 3, p. 18-26.
10. *Chen B. et al.* Thickness and dielectric constant of dead layer in Pt/(Ba<sub>0.7</sub>Sr<sub>0.3</sub>)TiO<sub>3</sub>/YBa<sub>2</sub>Cu<sub>3</sub>O<sub>7-x</sub> capacitor // *Applied Physics Letters*. – 2004, v. 84, № 4, p. 583-585.
11. *Vendik O.G., Zubko S.P., Ter-Martirosyan L.T.* Experimental evidence of the size effect in thin ferroelectric films // *Applied physics letters*. – 1998, v. 73, p. 37-39.
12. *Tyunina M., Levoska J.* Application of the interface capacitance model to thin-film relaxors and ferroelectrics // *Applied physics letters*. – 2006, v. 88. № 26, p. 262904-1-262904-3.
13. *Gerra G. et al.* Ionic polarizability of conductive metal oxides and critical thickness for ferroelectricity in BaTiO<sub>3</sub> // *Physical review letters*. – 2006, v. 96. № 10, p. 107603-1-107603-4.
14. *Hwang C.S. et al.* Depletion layer thickness and Schottky type carrier injection at the interface between Pt electrodes and (Ba, Sr) TiO<sub>3</sub> thin films // *Journal of applied physics*. – 1999, v. 85, № 1, p. 287-295.
15. *Kaleli B. et al.* Analysis of thin-film PZT/LNO stacks on an encapsulated TiN electrode // *Microelectronic engineering*. – 2014, v. 119, p. 16-19.
16. *Majdoub M.S., Maranganti R., Sharma P.* Understanding the origins of the intrinsic dead layer effect in nanocapacitors // *Physical Review B*. – 2009, v. 79, № 11, p. 115412-1-115412-8.
17. *Chang L.W. et al.* Size effects on thin film ferroelectrics: Experiments on isolated single crystal sheets // *Applied Physics Letters*. 2008, v. 93. № 13, p. 132904-1-132904-3.
18. *Лавров П.П.* Влияние пористости на сегнетоэлектрические свойства пленок цирконата-титаната свинца // *Фундаментальные проблемы радиоэлектронного приборостроения*. – 2015, т. 15, №. 2, с. 241-245.
19. *Tagantsev A.K., Gerra G.* Interface-induced phenomena in polarization response of ferroelectric thin films // *Journal of applied physics*. – 2006, т. 100, № 5, с. 051607-1-051607-28.
20. *Воротиллов К.А., Подгорный Ю.В., Сигзов А.С, Лавров П.П.* Вольтамперные характеристики пористых пленок ЦТС // *Нано- и микросистемная техника*. – 2014, № 9, с. 3-12.
21. *Podgorny Y. et al.* Leakage currents in porous PZT films // *Ferroelectrics*. – 2016, т. 503, № 1, с. 77-84.